

# **PHPT60603NY**

# 60V, 3 A NPN high power bipolar transistor

10 January 2014

**Product data sheet** 

### 1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60603PY

### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AECQ-101 qualified.

### 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- · Backlighting apllications

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	8	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C	-	60	90	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В
3	Е	emitter	[d	, M
4	В	base	و ق ق ق	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	- Sylli123

## 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT60603NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60603NY	0603NAB

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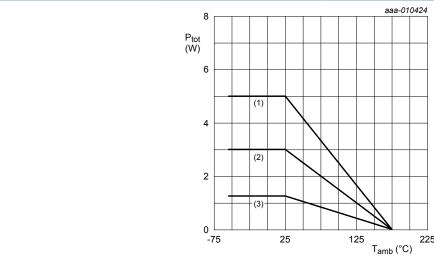
### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	60	V
$V_{CEO}$	collector-emitter voltage	open base		-	60	V
$V_{EBO}$	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	8	Α
I <sub>B</sub>	base current			-	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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PHPT60603NY

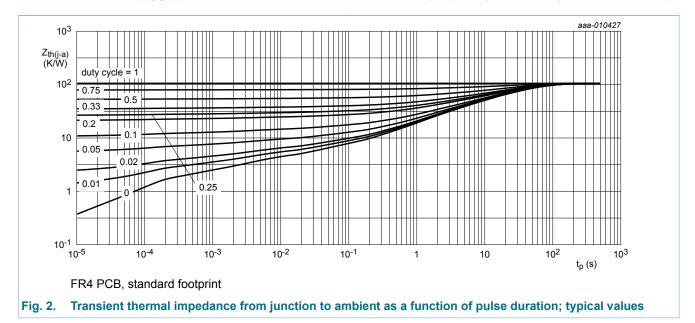
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### 9. Thermal characteristics

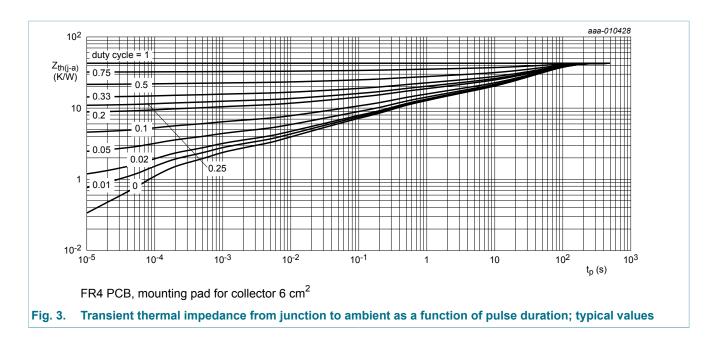
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	115	K/W
	from junction to ambient		[2]	-	-	50	K/W
	anibient		[3]	-	-	30	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



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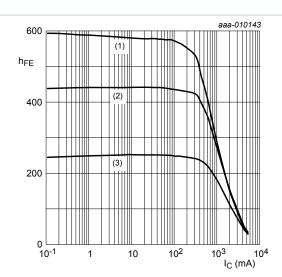
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### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; $T_{amb}$ = 25 °C	200	400	-	
		$V_{CE} = 2 \text{ V; } I_{C} = 1 \text{ A; } t_{p} \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	330	-	
		$V_{CE} = 2 \text{ V; } I_{C} = 2 \text{ A; } t_{p} \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	180	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 3 A; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	50	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 50 mA; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	70	120	mV
		I <sub>C</sub> = 3 A; I <sub>B</sub> = 300 mA; pulsed;	-	180	270	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	60	90	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}C$	-	0.86	1	V
		$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	1	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	0.65	0.85	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	120	-	ns
t <sub>on</sub>	turn-on time		-	135	-	ns
t <sub>s</sub>	storage time		-	800	-	ns
t <sub>f</sub>	fall time		-	300	-	ns
t <sub>off</sub>	turn-off time		-	1100	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	140	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	17	-	pF

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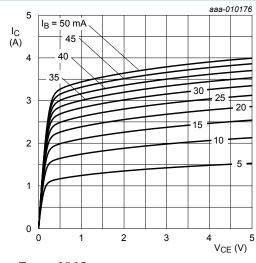
$$V_{CE} = 1 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

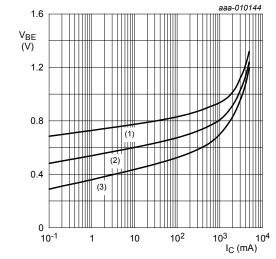
$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



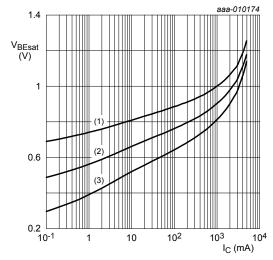
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

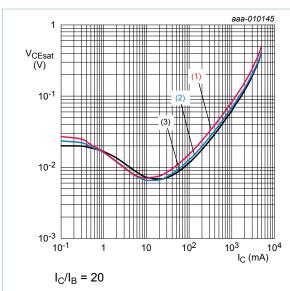
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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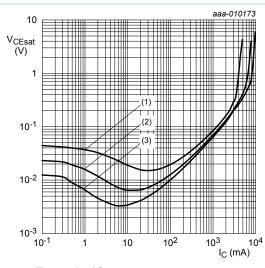


(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation resistance as a function of collector current; typical values



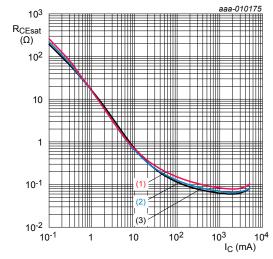
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 50$$

(2) 
$$I_C/I_B = 20$$

(3) 
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values



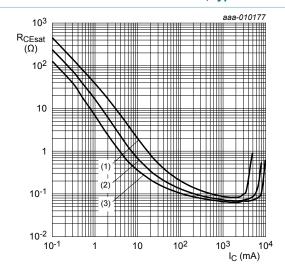
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 50$$

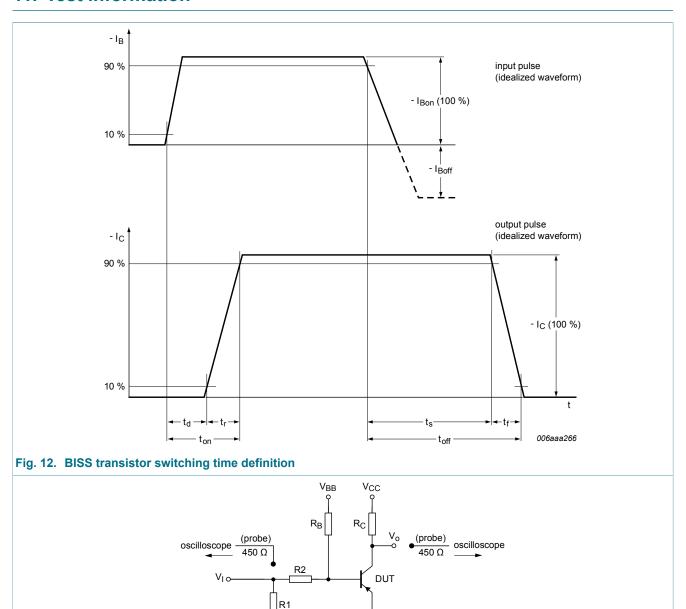
(2) 
$$I_C/I_B = 20$$

(3) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

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### 11. Test information



### 11.1 Quality information

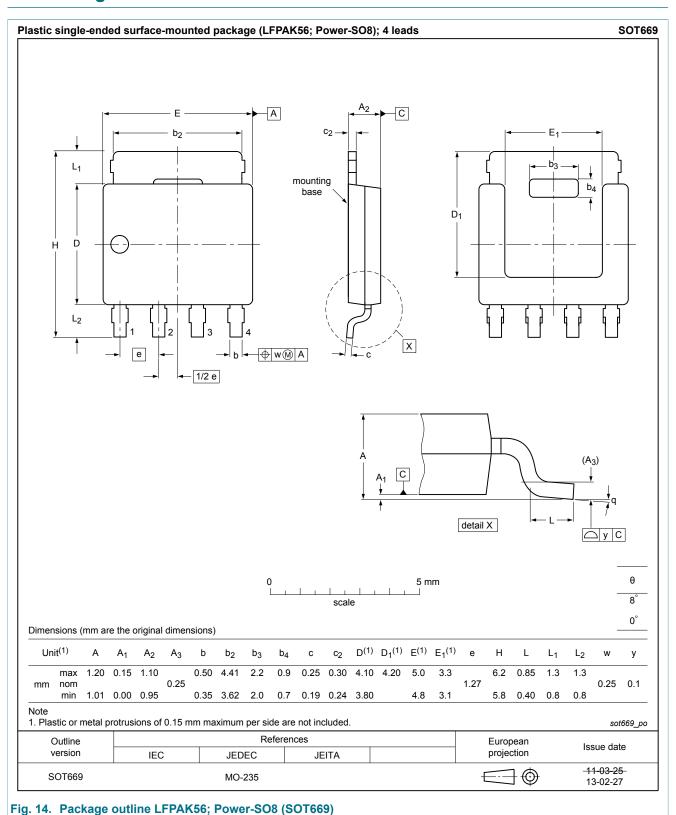
Fig. 13. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline

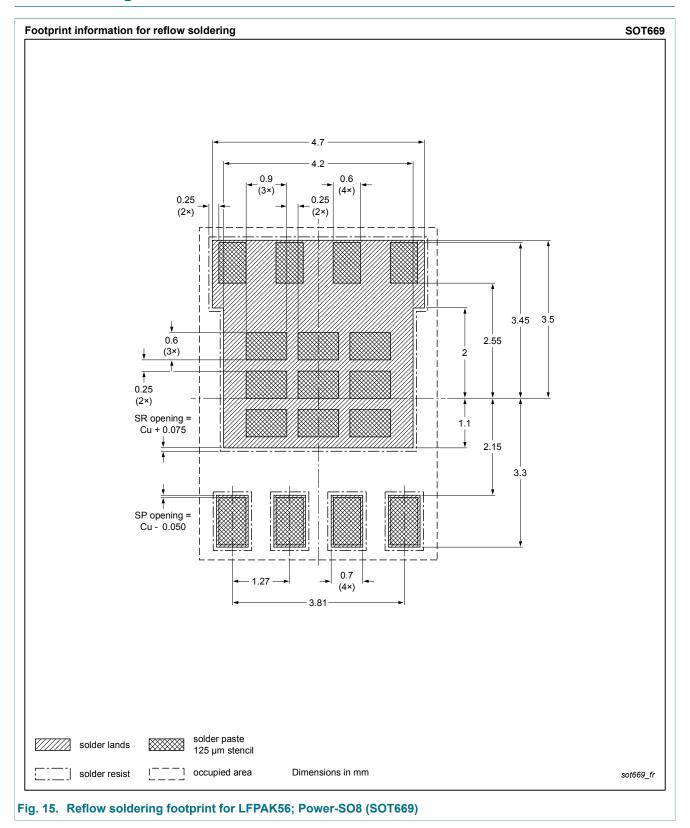


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### 13. Soldering



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## 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60603NY v.1	20131213	Product data sheet	-	-
Modifications:	editorial update			
PHPT60603NY v.2	20140110	Product data sheet	-	PHPT60603NY v.1

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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